



DTC114WE/DTC114WUA/DTC114WCA

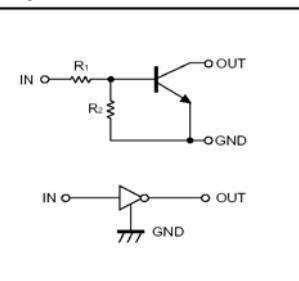
DTC114WKA/DTC114WSA

Digital Transistor(NPN)

Features

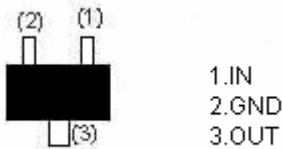
- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making device design easy.

● Equivalent circuit



PIN CONNECTIONS AND MARKING

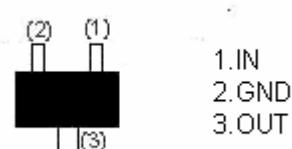
DTC114WE



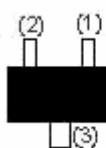
SOT-523

Addreviated symbol: 84

DTC114WUA



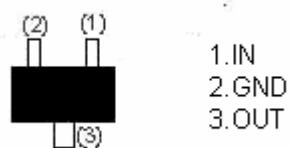
DTC114WKA



SOT-23-3L

Addreviated symbol: 84

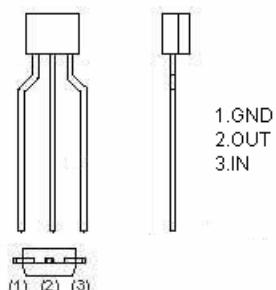
DTC114WCA



SOT-23

Addreviated symbol: 84

DTC114WSA



TO-92S



DTC114WE/DTC114WUA/DTC114WCA

DTC114WKA/DTC114WSA

Digital Transistor(NPN)

Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits (DTC114W)					Unit			
		E	UA	CA	KA	SA				
Supply voltage	V _{CC}	50					V			
Input voltage	V _{IN}	-10~30					V			
Output current	I _O	100					mA			
	I _{C(MAX)}	100								
Power dissipation	P _d	150	200			300	mW			
Junction temperature	T _j	150					°C			
Storage temperature	T _{stg}	-55~150					°C			

Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Input voltage	V _{I(off)}			0.8	V	V _{CC} =5V ,I _O =100μA
	V _{I(on)}	3				V _O =0.3V ,I _O =2 mA
Output voltage	V _{O(on)}		0.1	0.3	V	I _O /I _I =10mA/0.5mA
Input current	I _I			0.88	mA	V _I =5V
Output current	I _{O(off)}			0.5	μA	V _{CC} =50V, V _I =0
DC current gain	G _I	24				V _O =5V, I _O =10mA
Input resistance	R _I	7	10	13	KΩ	
Resistance ratio	R ₂ /R ₁	0.37	0.47	0.57		
Transition frequency	f _T		250		MHz	V _O =10V, I _O =5mA, f=100MHz